

Amendments to the Abstract

Kindly replace the original abstract (page 106) with the following substitute abstract (attached hereto).

Abstract

A method of producing an efficient nitride semiconductor element having an opposed terminal structure. The method includes a growing step for growing the nitride semiconductor further having an undoped GaN layer on a different materials substrate; subsequently, an attaching step for attaching the supporting substrate to the first conductive type nitride semiconductor layer side of the nitride semiconductor and interposing a first terminal between them; and subsequently, an exposing step for exposing the second conductive type nitride semiconductor layer by eliminating the different material substrate and the undoped GaN.